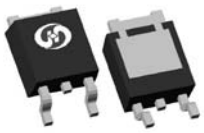
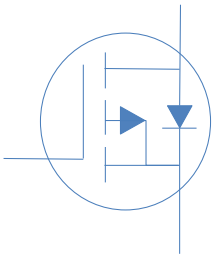
60V P-Ch Power MOSFET

			Ω
			Ω





=25 (unless otherwise specified)

		=25		
Avalanche Energy, Single Pulse	E			
Power Dissipation		=25		

Thermal Resistance Junction-Ambient	θ		/W
Thermal Resistance Junction-Case	θ		/W

Electrical Characteristics at T =25 (unless otherwise specified)

Static Characteristics

Drain to Source Breakdown Voltage		μ				
Gate Threshold Voltage	GS(th)	μ				
		=25				μ
		=125				
						Ω
	fs					
		=0V, f=1MHz				Ω

Dynamic Characteristics

		=-25V, f=1MHz				pF
Reverse Transfer Capacitance						
Total Gate Charge						
Gate to Source Charge						
Gate to Drain (Miller) Charge						
		Ω				
Turn off Delay Time	d(off)					
Fall Time	f					

Reverse Diode Characteristics

Diode Forward Voltage		F				
		F /dt=100A/μ				
Reverse Recovery Charge						

Fig 1. Typical Output Characteristics	Figure 2. On-Resistance vs. Gate-Source Voltage

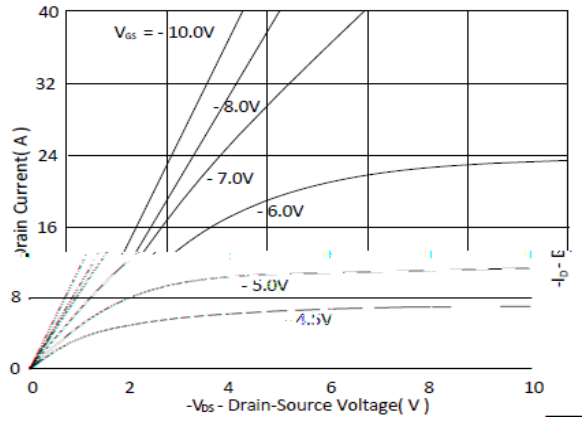
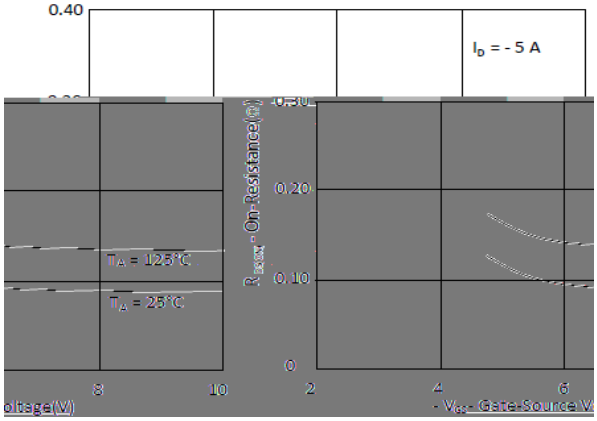

	

Figure 3. On-Resistance vs. Drain Current and Gate Voltage	Figure 4. Normalized On-Resistance vs. Junction Temperature

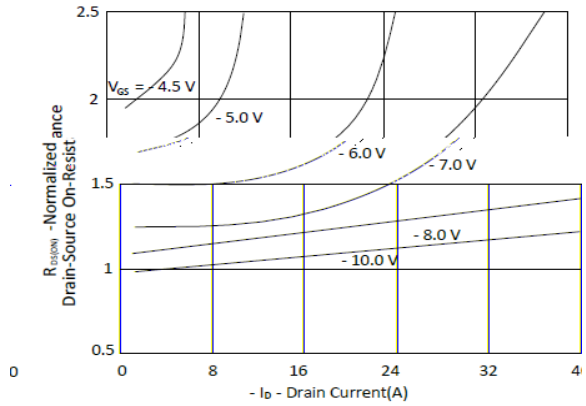
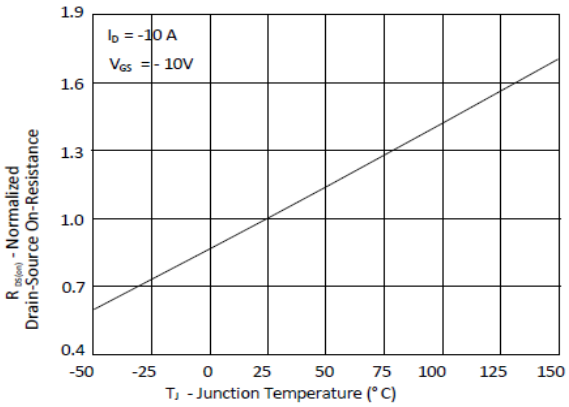

	

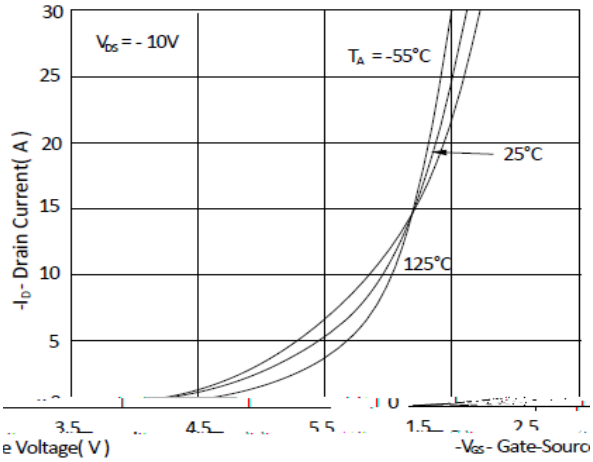
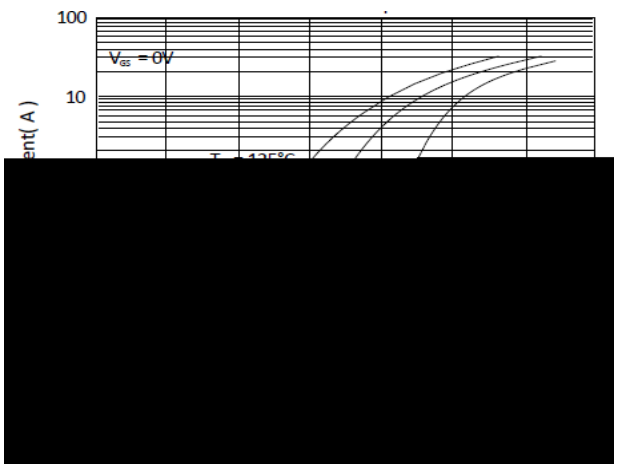
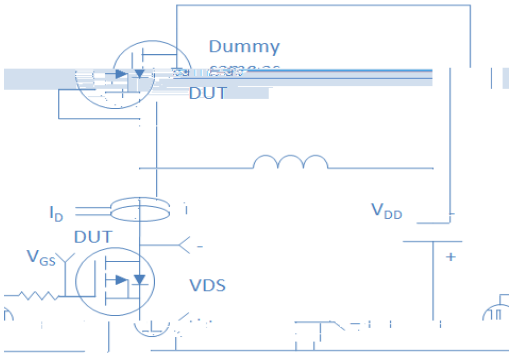
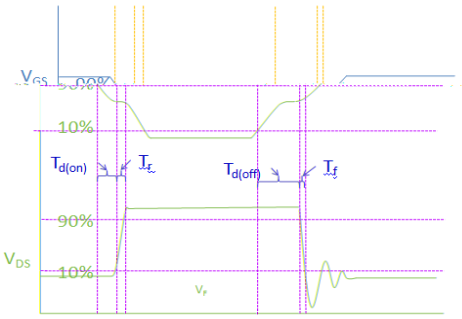
Figure 5. Typical Transfer Characteristics	Figure 6. Typical Source-Drain Diode Forward Voltage
	

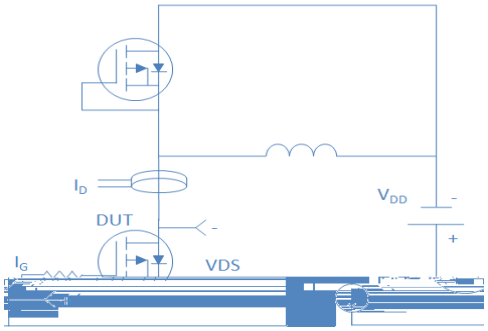
Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

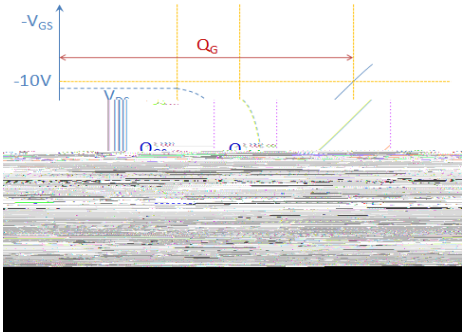
Inductive switching Test



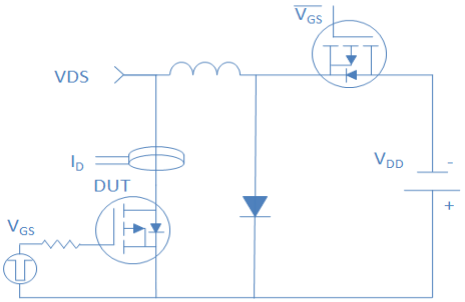


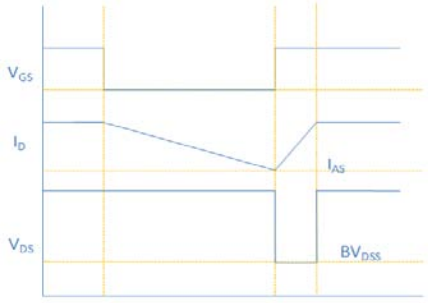
Gate Charge Test

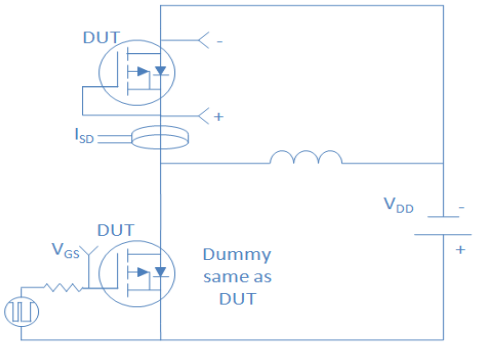


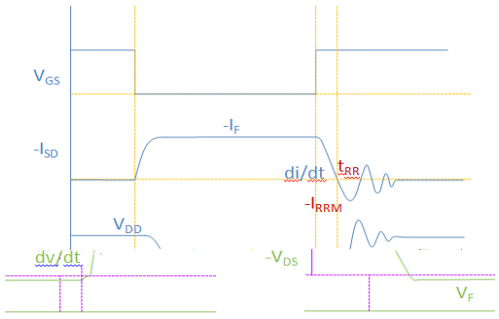


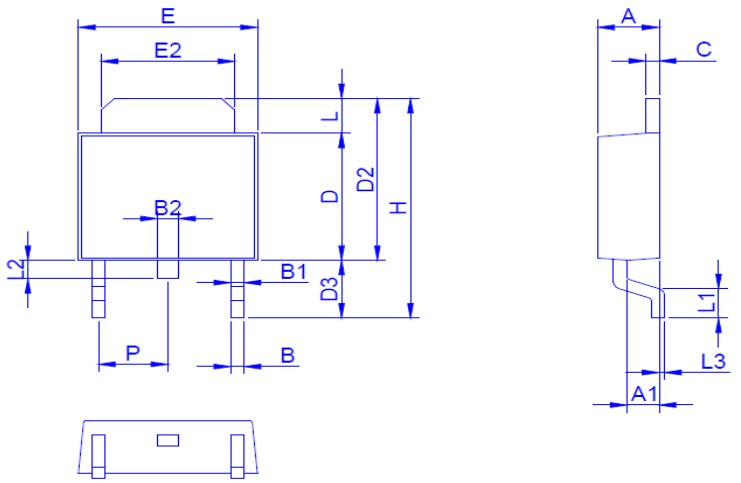
Uclamped Inductive Switching (UIS) Test











Dimension	A	A1	B	B1	B2	C	D	D2	D3	E	E2	H	L	L1	L2	L3	P
	0.60	0.40	5.30	6.70	2.20	6.40	4.80	9.20	0.89	0.90	0.50	0.00	2.10	Min.	2.10	0.95	0.30	0.40
	1.00	0.60	6.20	7.30	3.00	6.70	5.45	10.15	1.70	1.65	1.10	0.30	2.50	Max	2.50	1.30	0.85	0.94